

ROLE OF CU CONTENT IN THE CRYSTAL STRUCTURE AND PHASE STABILITY OF EPITAXIAL CU(IN,GA)S₂ FILMS ON GAP/SI(001)

Reference: E. Bertin et al., Mater Sci in Semicon Proc 166 (2023) 107685

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This work is supported by the French National Research Agency project EPCIS (Grant no. ANR-20-CE05-0038).

This study examines the growth condition to obtain a single-phase Cu(In,Ga)S2 (CIGS) chalcopyrite film epitaxially grown by coevaporation on a GaP/Si(001) pseudosubstrate. In particular, we report the structural differences between KCN-etched Cu-rich and Cu-poor CIGS films coevaporated on GaP/Si(001) by 1-stage process. The Cu-poor CIGS film consists of at least three phases; the main crystal is found to be chalcopyrite-ordered, coexisting with In-rich CuIn5S8, and CuAu-ordered CuInS2, all sharing epitaxial relationships with each other and the GaP/Si(001) pseudo-substrate. On the other hand, the Cu-rich CIGS film is single-phase chalcopyrite and displays sharper X-ray diffraction peaks and a lower density of microtwin defects. The elimination of the secondary CuAu-ordered phase with Cu excess is demonstrated. In both films, the chalcopyrite crystal exclusively grows with its c-axis aligned with the out-of-plane direction of Si[001]. This study confirms prior findings on the thermodynamics of Cu–In-Ga-S and the stability of secondary phases. This work paves the way to the future development of CIGS/Si tandem solar cells.

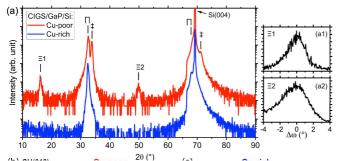
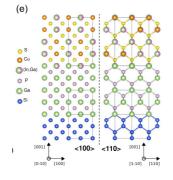


Fig. 2. (a) Low resolution longitudinal $\omega/2\theta$ scan along the [001] direction of the Si substrate. Transverse ω scans displaying the highly textures nature of the (a1) $\Xi 1$ and (a2) $\Xi 2$ CA peaks. (bc)



Schematics of the crystal stack [41] corresponding to the following epitaxial relationship: CH[100](001)//GaP[100](001)//Si[100](001).